

2SC2652

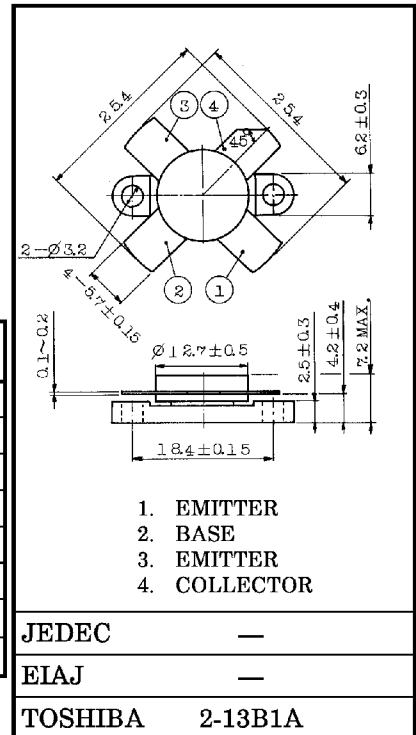
2~30MHz SSB LINEAR POWER AMPLIFIER APPLICATIONS
(50V SUPPLY VOLTAGE USE)

Unit in mm

- Specified 50V, 28MHz Characteristics
- Output Power : $P_o = 200W_{PEP}$
- Power Gain : $G_p = 13dB$ (Min.)
- Collector Efficiency : $\eta_C = 35%$ (Min.)
- Intermodulation Distortion : $IMD = -30dB$ (Max.)

MAXIMUM RATINGS (T_c = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	85	V
Collector-Emitter Voltage	V _{CES}	85	V
Collector-Emitter Voltage	V _{CEO}	55	V
Emitter-Base Voltage	V _{EBO}	4	V
Collector Current	I _C	20	A
Collector Power Dissipation	P _C	300	W
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _{stg}	-65~175	°C



ELECTRICAL CHARACTERISTICS (T_c = 25°C)

Weight : 5.2g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 100mA, I _B = 0	55	—	—	V
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	I _C = 100mA, V _{BE} = 0	85	—	—	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = 1mA, I _C = 0	4	—	—	V
DC Current Gain	h _{FE}	V _{CB} = 5V, I _C = 10A *	10	—	150	
Collector Output Capacitance	C _{ob}	V _{CB} = 50V, I _E = 0 f = 1MHz	—	300	—	pF
Power Gain	G _p	V _{CC} = 50V, f ₁ = 28.000MHz	13.0	15.2	—	dB
Input Power	P _i	f ₂ = 28.001MHz	—	6	10	W _{PEP}
Collector Efficiency	η _C	I _{idle} = 100mA	35	—	—	%
Intermodulation Distortion	IMD	P _o = 200W _{PEP} .(Fig.)	—	—	-30	dB
Series Equivalent Input Impedance	Z _{in}	V _{CC} = 50V, f = 28MHz	—	1.15 -j1.15	—	Ω
Series Equivalent Output Impedance	Z _{out}	Δf = 1kHz, P _o = 200W _{PEP}	—	5.4 -j2.0	—	Ω

* Pulse Test : Pulse Width ≤ 100μs, Duty Cycle ≤ 3%

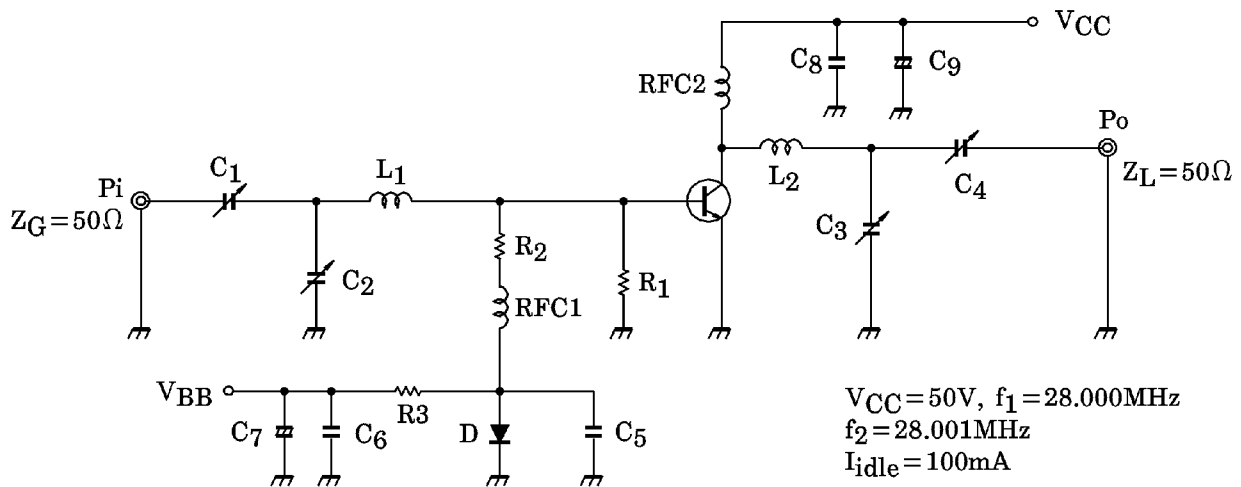
CAUTION

Beryllia Ceramics is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this properly according to law. Do not intermingle with normal industrial or domestic waste.

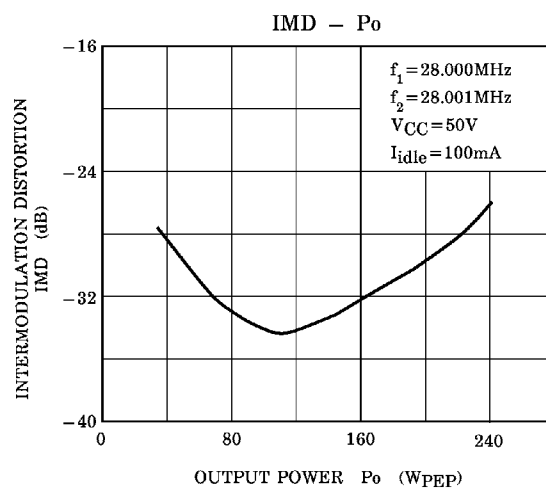
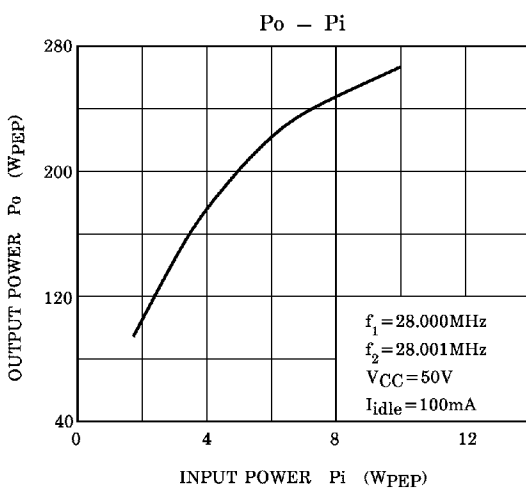
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Fig. Pi TEST CIRCUIT



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| C ₁ , C ₂ : 7~150pF | L ₁ : φ0.8 ENAMEL COATED COPPER WIRE, 14ID, 4T, 4P |
| C ₃ , C ₄ : 7~150pF 2KWV | L ₂ : φ1.2 ENAMEL COATED COPPER WIRE, 14ID, 3 1 / 2T, 3P |
| C ₅ , C ₆ : 0.022μF | RFC ₁ : φ0.8 ENAMEL COATED COPPER WIRE, 10ID, 9T
(Ferrite Core TDK K2) |
| C ₇ : 47μF 10WV | RFC ₂ : φ0.8 ENAMEL COATED COPPER WIRE, 14ID, 20T |
| C ₈ : 0.044μF | R ₁ : 10Ω (1W) |
| C ₉ : 100μF 50WV | R ₂ : 2Ω (1 / 2W) |
| | R ₃ : 10Ω (5W) |
| | D : 1S1555 |



CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.

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